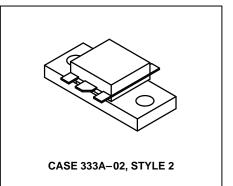
# The RF Line NPN Silicon RF Power Transistor

The MRF6414 is designed for 26 volt UHF large signal, common emitter, class AB linear amplifier applications.

- Specified 26 Volt, 960 MHz Characteristics Output Power = 50 Watts Minimum Gain = 8.5 dB @ 960 MHz, Class AB Minimum Efficiency = 50% @ 960 MHz, 50 Watts
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration



50 W, 960 MHz RF POWER TRANSISTOR NPN SILICON



### **MAXIMUM RATINGS**

Rating			Value		Unit
Collector–Emitter Voltage		VCEO	28		Vdc
Collector-Base Voltage		V <sub>CBO</sub>	65		Vdc
Emitter-Base Voltage		V <sub>EBO</sub>	4		Vdc
Collector-Current — Continuous		ιc	6		Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C		PD	134 0.77		Watts W/°C
Storage Temperature Range		T <sub>stg</sub>	-65 to +150		°C
THERMAL CHARACTERISTICS					
Characteristic		Symbol	Max		Unit
Thermal Resistance, Junction to Case		R <sub>θ</sub> JC	1.3		°C/W
ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}C$ unless otherwise	se noted)				-
Characteristic	Symbol	Min	Тур	Max	Unit
DFF CHARACTERISTICS				•	
Collector–Emitter Breakdown Voltage ( $I_C = 20 \text{ mAdc}, I_B = 0$ )	V(BR)CEO	28	_	_	Vdc
Collector–Base Breakdown Voltage ( $I_C = 20 \text{ mAdc}, I_E = 0$ )	V(BR)CBO	65	_	_	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 10 mAdc, I <sub>C</sub> = 0)	V(BR)EBO	4	_	—	Vdc
Collector–Emitter Leakage Current ( $V_{CE}$ = 30 Vdc, $R_{BE}$ = 75 $\Omega$ )	ICER	_	_	10	mAdc
DN CHARACTERISTICS	•	•		•	•
DC Current Gain (I <sub>CE</sub> = 1 Adc, V <sub>CE</sub> = 5 Vdc)	hFE	30	_	120	_



## **ELECTRICAL CHARACTERISTICS** — continued ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
DYNAMIC CHARACTERISTICS					
Output Capacitance (V <sub>CB</sub> = 26 Vdc, I <sub>E</sub> = 0, f = 1 MHz) (1)	C <sub>ob</sub>	—	45	—	pF
FUNCTIONAL TESTS	•				
Common–Emitter Amplifier Power Gain (V <sub>CC</sub> = 26 Vdc, P <sub>out</sub> = 50 W, I <sub>CQ</sub> = 200 mA, f = 960 MHz)	G <sub>pe</sub>	8.5	_	_	dB
Collector Efficiency (V <sub>CC</sub> = 26 Vdc, P <sub>out</sub> = 50 W, I <sub>CQ</sub> = 200 mA, f = 960 MHz)	η	50	55	_	%
Output Mismatch Stress (V <sub>CC</sub> = 26 Vdc, P <sub>OUt</sub> = 50 W, I <sub>CQ</sub> = 200 mA, f = 960 MHz) VSWR = 3:1; all phase angles at frequency of test	Ψ	No Degradation in Output Power			

(1) For information only. It is not measurable in MRF6414 because of internal matching network.

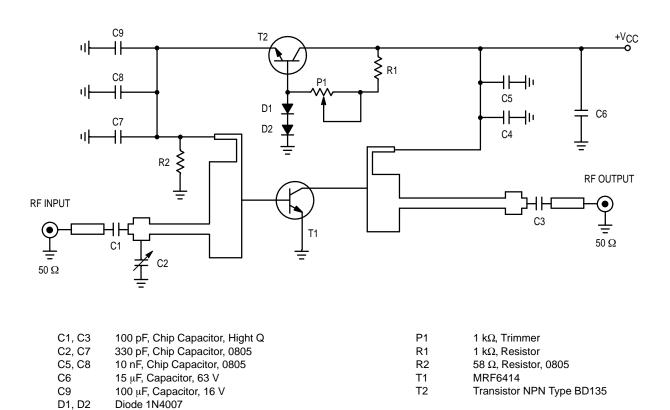


Figure 1. 960 MHz Test Circuit Schematic

# **TYPICAL CHARACTERISTICS**

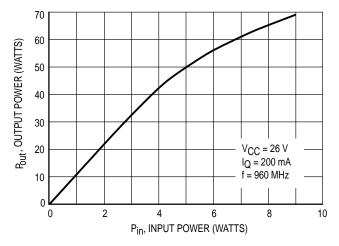


Figure 2. Output Power versus Input Power (Typical)

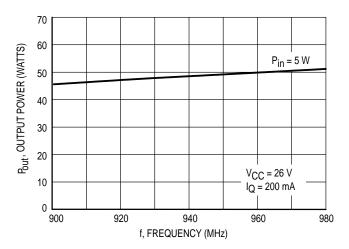


Figure 3. Output Power versus Frequency

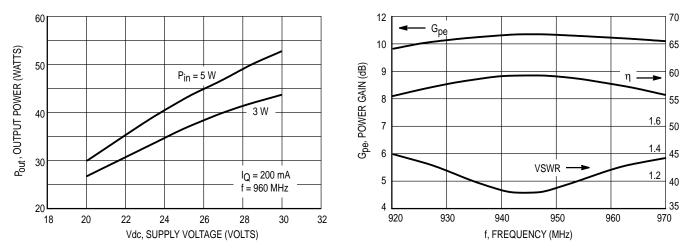
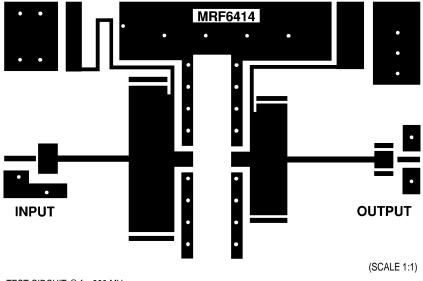


Figure 4. Output Power versus Supply Voltage

Figure 5. Typical Broadband Amplifier



TEST CIRCUIT @ f = 960 MHz TEFLON  $^{(\!R\!)}$  GLASS 1/50 INCH Er = 2.55

Figure 6. MRF6414 Photomaster (Reduced 25% in printed data book, DL110/D)

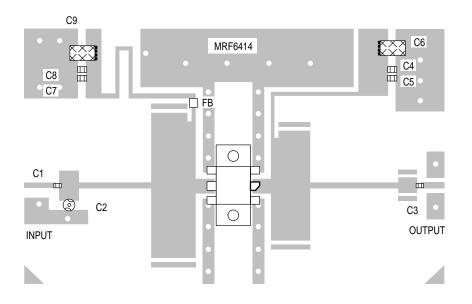
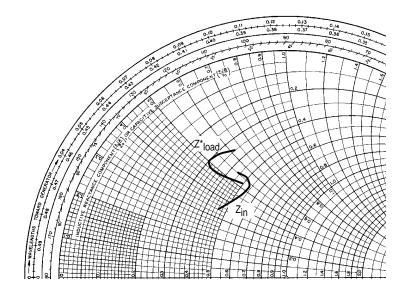


Figure 7. 960 MHz Test Circuit Components Layout

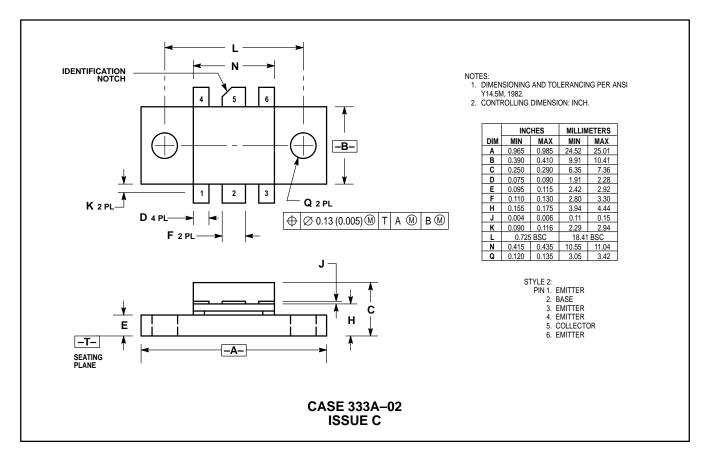


f MHz	Z <sub>in</sub> Ohms	Z <sub>OL</sub> * Ohms
900	4.4 + j4.6	4.7 + j4.7
935	5.1 + j4.8	4.0 + j3.9
960	5.4 + j3.6	3.7 + j4.5
980	4.7 + j2.5	3.4 + j4.7

Z<sub>OL</sub>\*: Conjugate of optimum load impedance into which the device operates at a given output power, voltage, current and frequency.

Figure 8. Input and Output Impedances with Circuit Tuned for Maximum Gain @ V\_CC = 26 V, I\_Q = 200 mA, P\_out = 50 W

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#### How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution; P.O. Box 5405, Denver, Colorado 80217. 1–303–675–2140 or 1–800–441–2447

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4–32–1 Nishi–Gotanda, Shagawa–ku, Tokyo, Japan. 03–5487–8488

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